



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _C = +25°C	
	$2m\Omega$ @ $V_{GS} = 10V$	205A	
60V	$3m\Omega @ V_{GS} = 6V$	170A	
	$3.3 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	165A	

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
 - Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

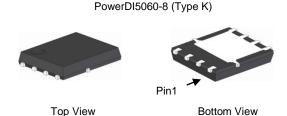
Description and Applications

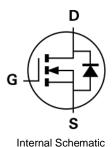
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

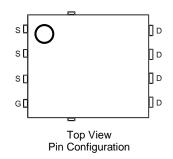
- Switching
- Synchronous Rectification
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208®3
- Weight: 0.097 grams (Approximate)







Ordering Information (Note 4)

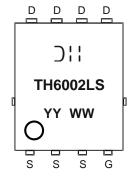
- 7			
	Part Number	Case	Packaging
	DMTH6002LPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- <1000ppm antimony compounds.

 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ H = Manufacturer's Marking
TH6002LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_C = +25$ °C $T_C = +100$ °C	ID	205 145	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	820	Α	
Continuous Body Diode Forward Current (Note 6)	Tc = +25°C	Is	205	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	820	Α	
Avalanche Current, L = 3mH	las	14	Α	
Avalanche Energy, L = 3mH	E _{AS}	294	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	PD	3	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		$R_{\theta JA}$	50	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	PD	167	W
Thermal Resistance, Junction to Case (Note 6)	Rejc	0.9	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

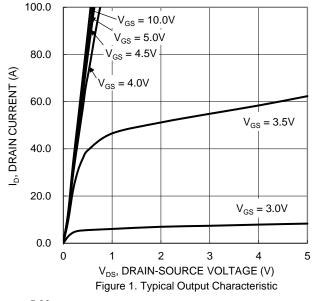
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
		_	1.7	2		V _G S = 10V, I _D = 30A
Static Drain-Source On-Resistance	RDS(ON)	_	2	3	mΩ	$V_{GS} = 6V, I_{D} = 30A$
		_	2.3	3.3		$V_{GS} = 4.5V, I_D = 30A$
Diode Forward Voltage	VsD	_	_	1.2	V	V _G S = 0V, I _S = 50A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	6555	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	_	2264	_	pF	
Reverse Transfer Capacitance	Crss	_	187	_		
Gate Resistance	Rg	_	0.7	_	Ω V _{DS} = 0V, V _{GS} = 0V, f = 1MH	
Total Gate Charge (V _{GS} = 10V)	Q_g	_	130.8	_		V _{DS} = 30V, I _D = 50A
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	63.6	_	nC	
Gate-Source Charge	Qgs	_	20.8	_	nc	
Gate-Drain Charge	Q_{gd}	_	29.4	_		
Turn-On Delay Time	tD(ON)	_	11.2	_		
Turn-On Rise Time	t _R	_	10.8	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{g} = 2.5\Omega$
Turn-Off Delay Time	tD(OFF)	_	44	_	ns	
Turn-Off Fall Time	tF	_	19.5	_		
Reverse Recovery Time	trr	_	61.8	_	ns	I= 500 di/dt 1000/up
Reverse Recovery Charge	Q _{RR}	_	123	_	nC	-I _F = 50A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.

DMTH6002LPS





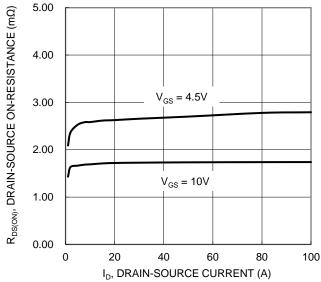


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

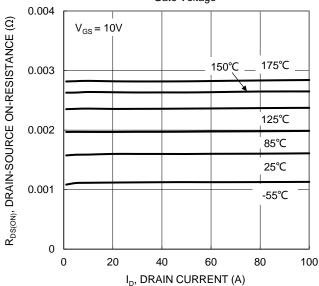
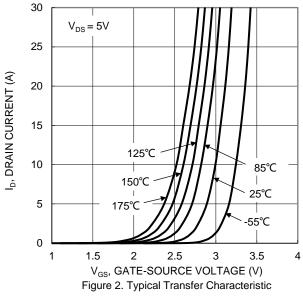
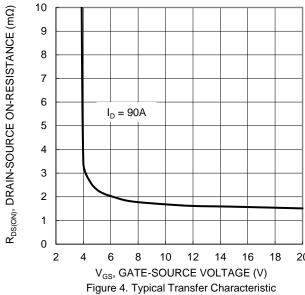


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





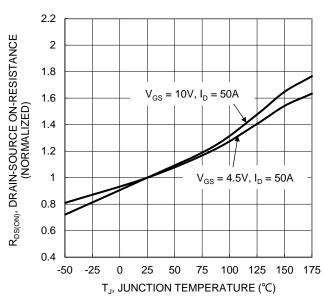


Figure 6. On-Resistance Variation with Temperature





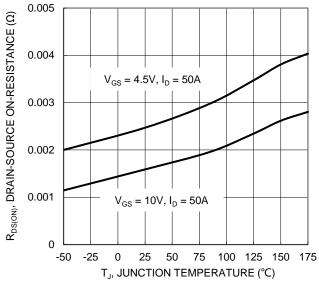
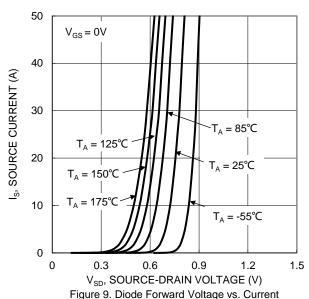


Figure 7. On-Resistance Variation with Temperature



10 8 6 $V_{GS}(V)$ 4 $V_{DS} = 30V, I_{D} = 50A$ 2 0 0 30 120 60 90 150 Q_{α} (nC) Figure 11. Gate Charge

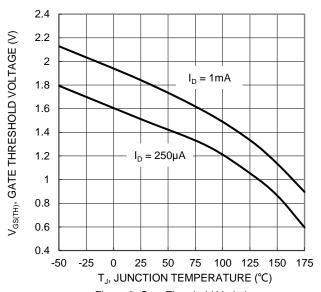
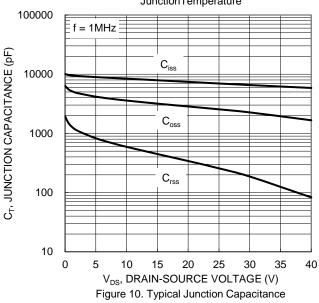


Figure 8. Gate Threshold Variation vs. JunctionTemperature



1000 R_{DS(ON)} Limited 100 DRAIN CURRENT (A) 10 =10ms 1 P_W =100ms T_{J(Max)} = 175 °C DC T_C = 25°C ۵_ 0.1 Single Pulse DUT on Infinite Heatsink $V_{GS} = 10V$ 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



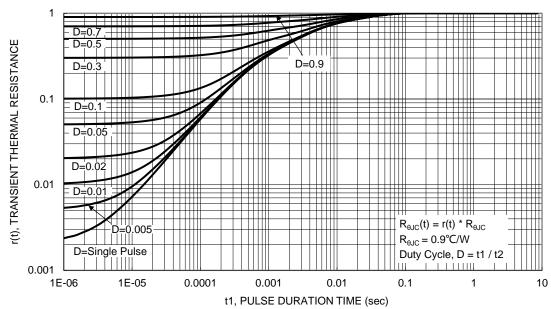


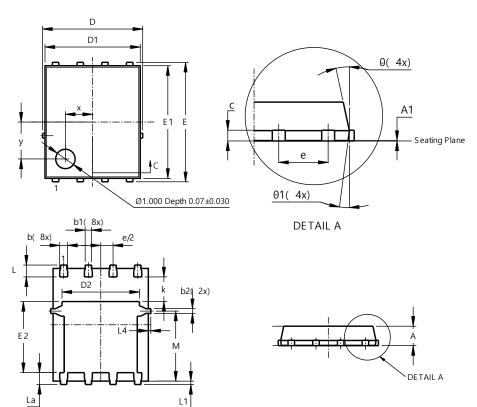
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

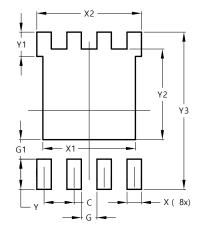


PowerDI5060-8 (Type K)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0			
D1	4.85	4.95	4.90		
D2	-	- 3.98			
Е	6	.15 BS0	\sim		
E1	5.75	5.85	5.80		
E2	3.56	3.725	3.66		
е	1	.27BSC	;		
k	-	-	1.27		
L	0.51	0.71	0.61		
La	0.51	0.675	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
Х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
C	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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